

Features

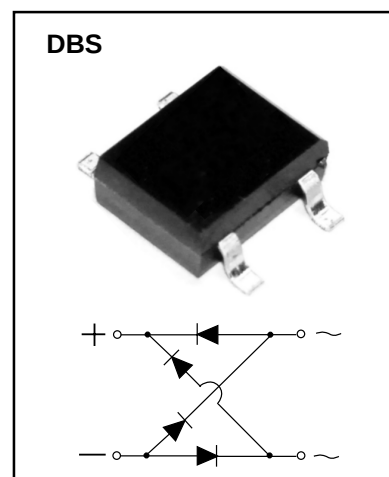
- $I_{F(AV)}$ 1.5A
- V_{RRM} 50V-1000V
- High surge current capability
- Glass passivated chip

Applications

- General purpose 1 phase Bridge rectifier applications

Marking

- DB15XS
- X : From 01 To 7

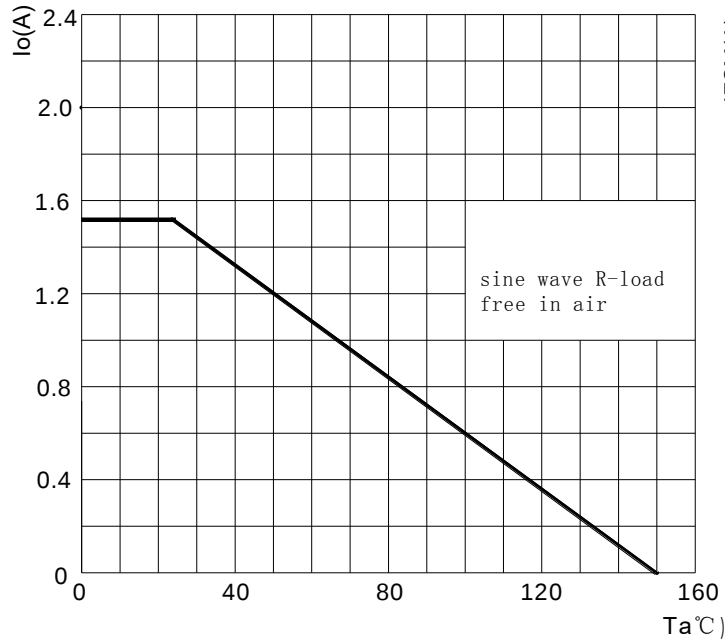
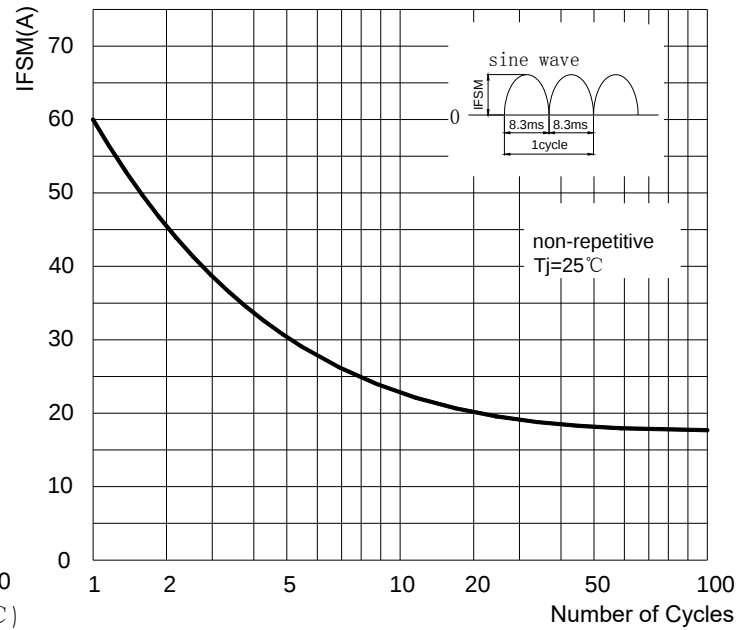
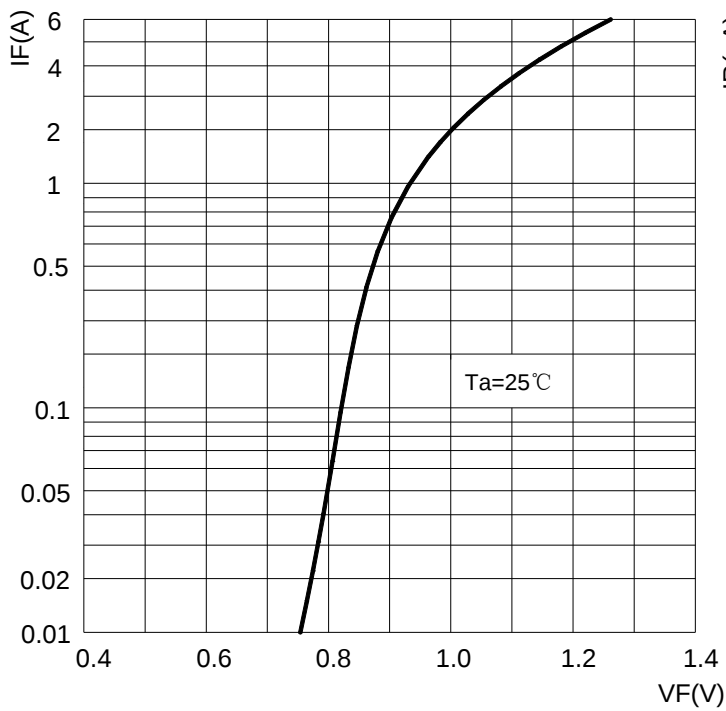
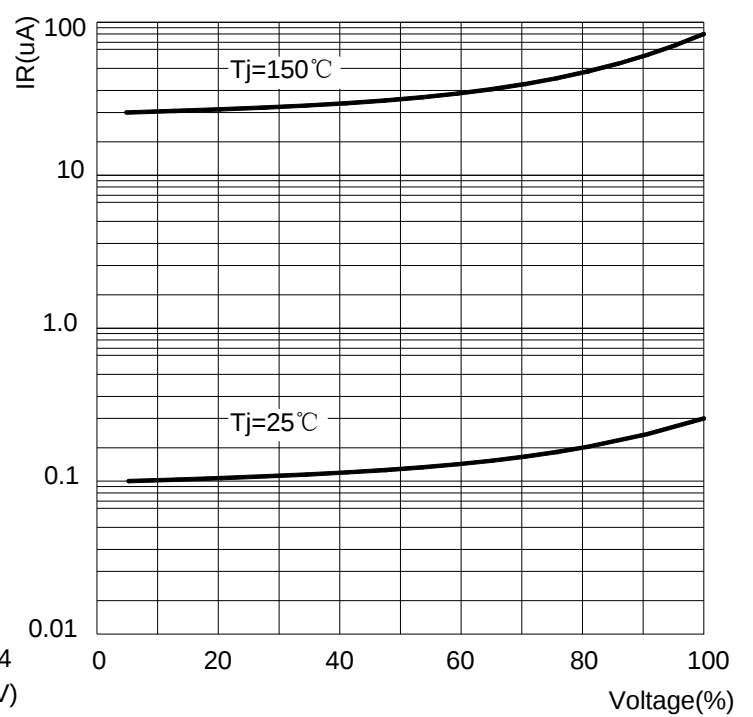


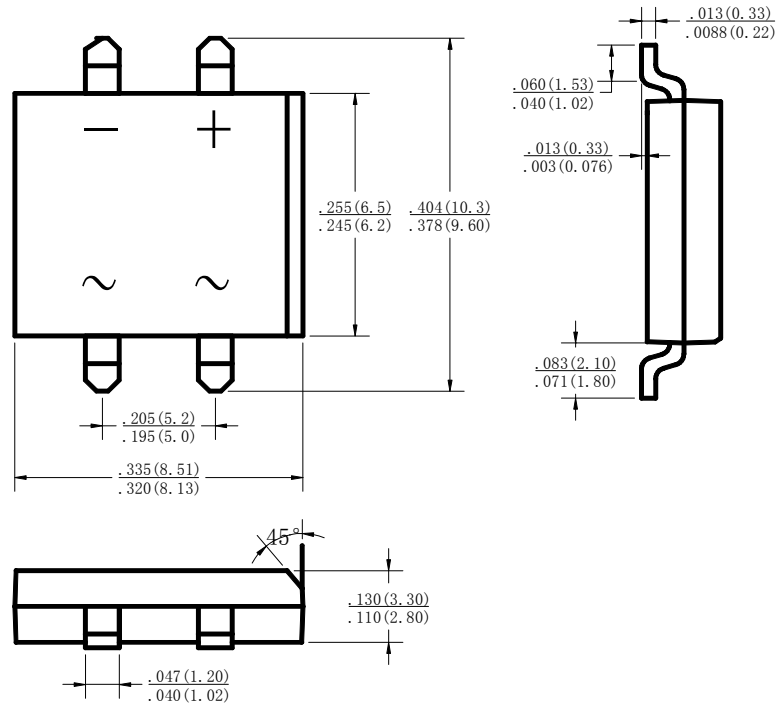
Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	DB15						
				1S	2S	3S	4S	5S	6S	7S
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Average Rectified Output Current	I_O	A	60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	On glass-epoxy substrate						
Surge(Non-repetitive) Forward Current	I_{FSM}	A	60Hz half sine wave, 1 cycle, $T_j=25^\circ\text{C}$	1.5						
Current Squared Time	I^2t	A^2S	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, Rating of per diode	60						
Operation Junction and Storage Temperature Range	T_j, T_{stg}	$^\circ\text{C}$		15						
				-55 ~ +150						

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

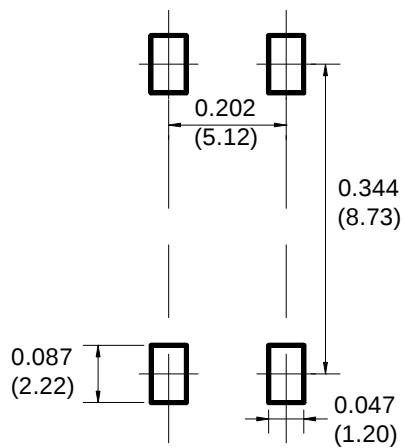
Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	$I_{FM}=1.5\text{A}$, Pulse measurement, Rating of per diode	1.1
Peak Reverse Current	I_{RRM}	μA	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C/W}$	Between junction and ambient, On glass-epoxy substrate	68
	$R_{\theta J-L}$		Between junction and lead	15

Typical Characteristics
FIG.1: FORWARD CURRENT DERATING CURVE

FIG.2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

FIG.3: TYPICAL FORWARD CHARACTERISTICS

FIG.4: TYPICAL REVERSE CHARACTERISTICS




Dimensions in inches and (millimeters)

DBS Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.